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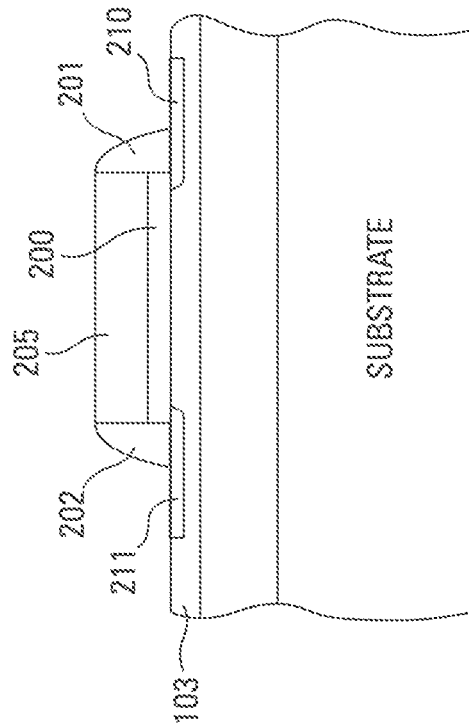


FIG. 1

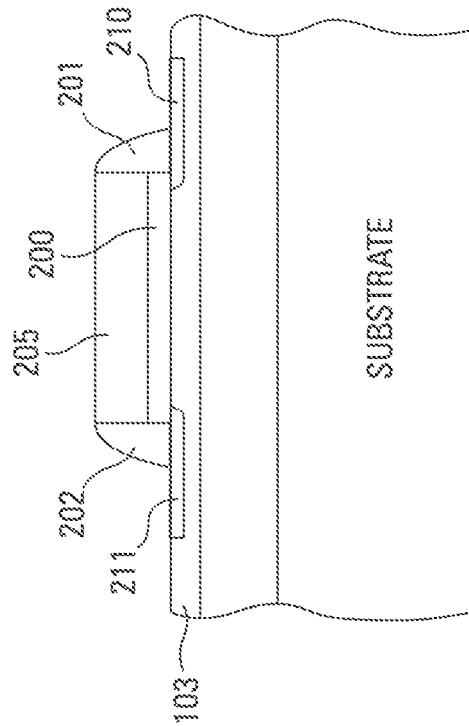


FIG. 2

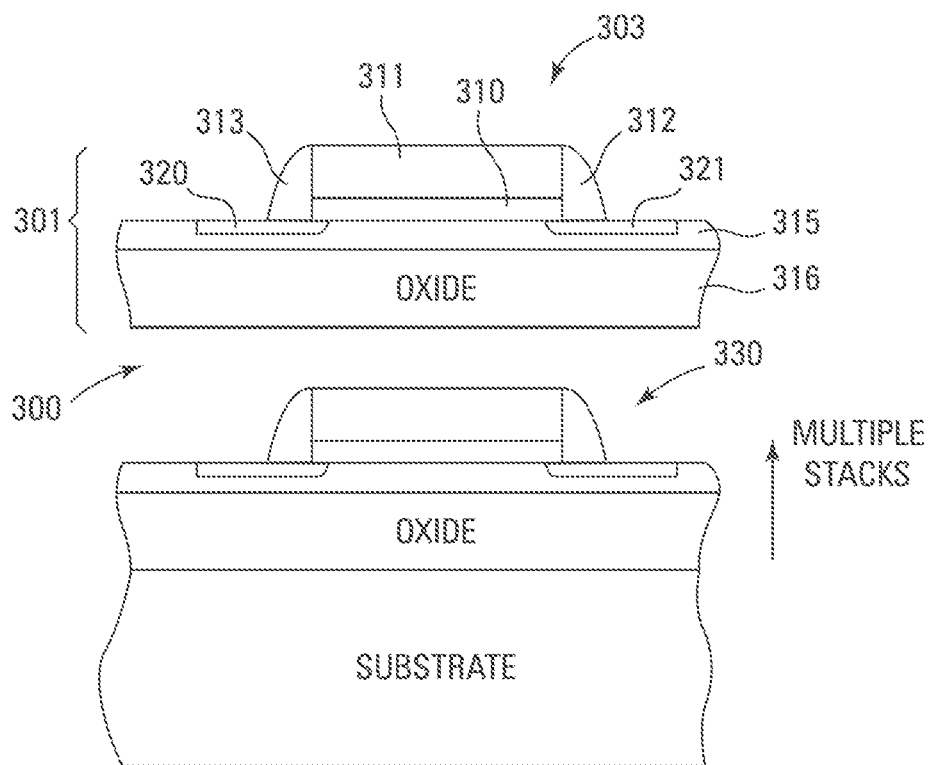


FIG. 3

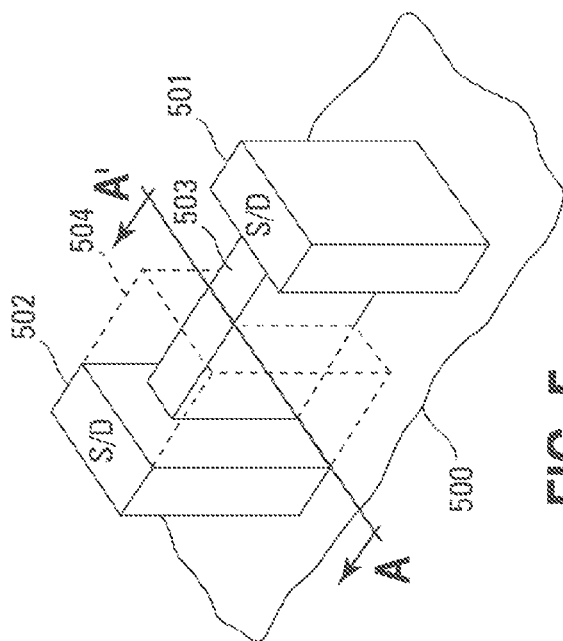


FIG. 5

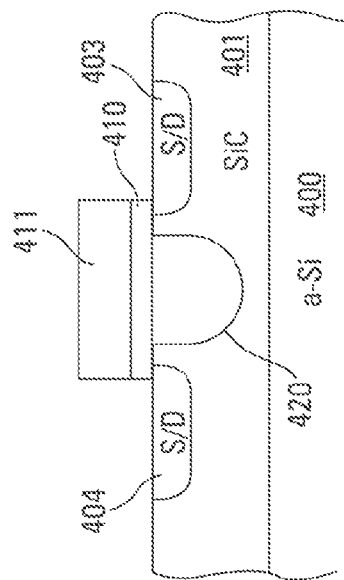


FIG. 4

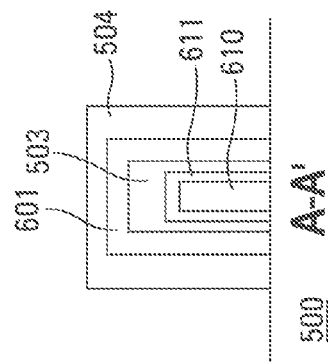


FIG. 6

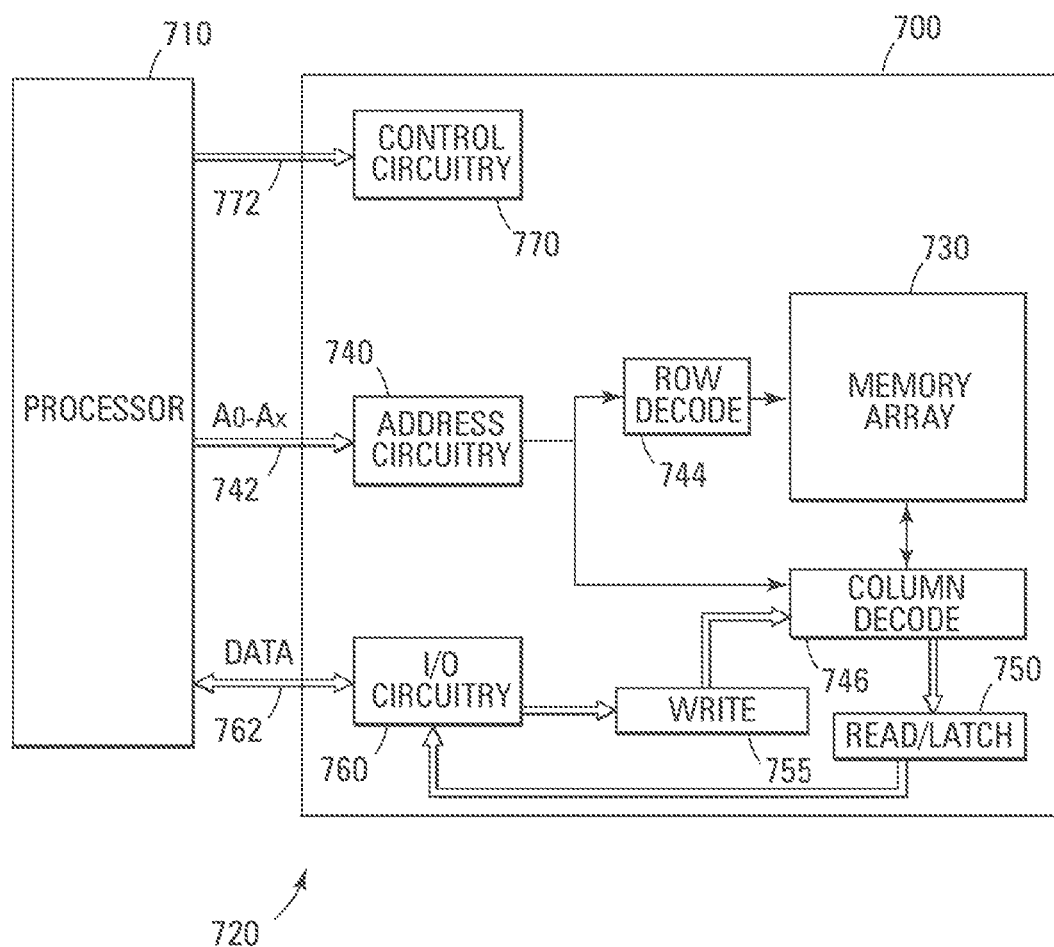


FIG. 7

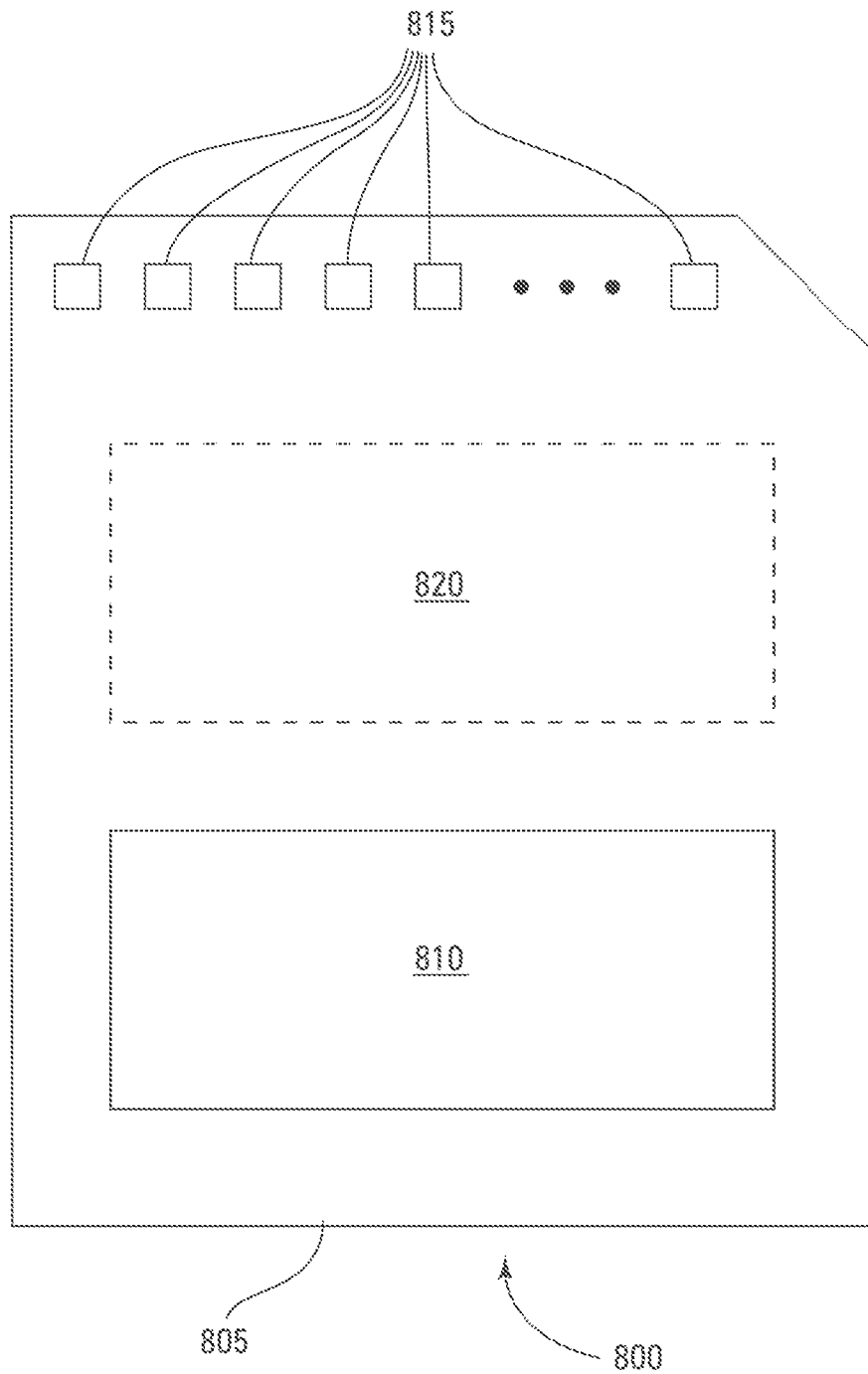


FIG. 8

# MEMORY WITH CARBON-CONTAINING SILICON CHANNEL

## RELATED APPLICATIONS

This is a continuation of U.S. patent application Ser. No. 13/849,962 titled "STACKED NON-VOLATILE MEMORY WITH SILICON CARBIDE-BASED AMORPHOUS SILICON THIN FILM TRANSISTORS," filed Mar. 25, 2013 (pending), which is a divisional of U.S. patent application Ser. No. 13/186,822 titled "STACKED NON-VOLATILE MEMORY WITH SILICON CARBIDE-BASED AMORPHOUS SILICON THIN FILM TRANSISTORS," filed Jul. 20, 2011, now U.S. Pat. No. 8,404,536, which is a continuation of U.S. patent application Ser. No. 12/235,970 titled "STACKED NON-VOLATILE MEMORY WITH SILICON CARBIDE-BASED AMORPHOUS SILICON THIN FILM TRANSISTORS," filed Sep. 23, 2008, now U.S. Pat. No. 7,994,566, which is a continuation of U.S. patent application Ser. No. 11/377,158 titled "STACKED NON-VOLATILE MEMORY WITH SILICON CARBIDE-BASED AMORPHOUS SILICON THIN FILM TRANSISTORS" filed Mar. 16, 2006, now U.S. Pat. No. 7,439,594, each of which is commonly assigned and incorporated herein by reference.

## TECHNICAL FIELD

The present invention relates generally to memory devices and in particular the present invention relates to non-volatile memory device architecture.

## BACKGROUND

Memory devices are typically provided as internal, semiconductor, integrated circuits in computers or other electronic devices. There are many different types of memory including random-access memory (RAM), read only memory (ROM), dynamic random access memory (DRAM), synchronous dynamic random access memory (SDRAM), and flash memory.

Flash memory devices have developed into a popular source of non-volatile memory for a wide range of electronic applications. Flash memory devices typically use a one-transistor memory cell that allows for high memory densities, high reliability, and low power consumption. Common uses for flash memory include personal computers, personal digital assistants (PDAs), digital cameras, and cellular telephones. Program code and system data such as a basic input/output system (BIOS) are typically stored in flash memory devices for use in personal computer systems.

The performance of flash memory devices needs to increase as the performance of computer systems increase. For example, a flash memory transistor that can be erased faster with lower voltages and have longer retention times could increase system performance.

Amorphous silicon (a-Si)-based thin film transistors (TFT) have been used to improve transistor performance. However, these transistors have undesirable short channel effects and randomness in device characteristics. This is largely due to the randomness in polysilicon grain size and grain boundaries that exist in TFT devices. For example, in sub-75 nm feature sizes, this can result in a very large variation in device characteristics making the stacked cell approach extremely challenging for mass manufacture.

Silicon carbide (SiC) substrates have been used in power devices due to the higher bandgap over silicon. Wide bandgap material like SiC substrates have very low intrinsic carrier

concentration and thermal generation scales directly with the intrinsic carrier concentration. Therefore, junction leakage currents in SiC substrate devices are very low.

However, SiC substrates suffer numerous problems. For example, wafer sizes in excess of four inches that have high quality and low cost are difficult to achieve. Additionally, the defect densities are unacceptable and the substrates suffer from poor carrier mobility for high speed switching.

For the reasons stated above, and for other reasons stated below which will become apparent to those skilled in the art upon reading and understanding the present specification, there is a need in the art for a higher performance flash memory transistor that does not have serious scaling issues.

## BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 shows a cross-sectional view of one embodiment of one or more steps in a method for fabrication of a memory device of the present invention.

FIG. 2 shows a cross-sectional view of one embodiment of one or more steps in the method for fabrication of the memory device of the present invention.

FIG. 3 shows a cross-sectional view of one embodiment of one or more steps in the method for fabrication of the memory device of the present invention.

FIG. 4 shows a cross-sectional view of one embodiment of a three dimensional transistor of the present invention.

FIG. 5 shows a perspective view of a FinFET embodiment of the present invention.

FIG. 6 shows a cross-sectional view of the embodiment of FIG. 5.

FIG. 7 shows a block diagram of an electronic memory system of the present invention.

FIG. 8 shows a block diagram of one embodiment of a memory module of the present invention.

## DETAILED DESCRIPTION

In the following detailed description of the preferred embodiments, reference is made to the accompanying drawings that form a part hereof, and in which is shown by way of illustration specific preferred embodiments in which the inventions may be practiced. These embodiments are described in sufficient detail to enable those skilled in the art to practice the invention, and it is to be understood that other embodiments may be utilized and that logical, mechanical and electrical changes may be made without departing from the spirit and scope of the present invention. The terms wafer and substrate used previously and in the following description include any base semiconductor structure. Both are to be understood as including bulk silicon, silicon-on-sapphire (SOS) technology, silicon-on-insulator (SOI) technology, silicon-on-nothing, thin film transistor (TFT) technology, doped and undoped semiconductors, epitaxial layers of silicon supported by a base semiconductor, as well as other semiconductor structures well known to one skilled in the art. Furthermore, when reference is made to a wafer or substrate in the following description, previous process steps may have been utilized to form regions/junctions in the base semiconductor structure. The following detailed description is, therefore, not to be taken in a limiting sense, and the scope of the present invention is defined only by the claims and equivalents thereof.

FIG. 1 illustrates a cross-sectional view of one embodiment of one or more steps for fabricating a memory device of the present invention. A substrate 100 undergoes standard CMOS processing for substrate isolation, well implants, and,

if needed, threshold voltage adjustments. All periphery logic devices are preferably formed in starting silicon substrate—bulk or SOI.

In one embodiment, the substrate **100** is a p-type substrate with n-wells having p-type regions. Alternate embodiments may use other conductivity types.

The periphery regions are covered and hard mask and lithography steps used to open up the memory array. An insulation layer **102** is formed over the substrate/well **100**. In one embodiment, this is an oxide layer **102**. Alternate embodiments may use other insulating materials for the insulation layer **102**.

A silicon carbide (SiC) and/or carbon rich amorphous silicon (a-Si) layer **103** is formed over the insulation layer **102**. This film **103** forms the channel region of the memory transistors of the present invention. The carbon concentration in the film **103** is tuned by controlling the SiC growth temperature. In an alternate embodiment, the SiC thin film is formed by direct deposition to form the channel region. In yet another embodiment, the SiC is formed after the a-Si deposition.

In still another alternate embodiment, the SiC is formed on silicon-germanium (a-SiGe) after deposition. In one version of this embodiment, the mole fraction of SiGe is tuned along with the SiC content to optimize carrier mobility.

In yet another embodiment, the SiC thin film is formed on hydrogenated a-Si (a-Si:H). Another embodiment forms the SiC thin film on deuterated a-Si (a-Si:D) and/or fluorinated a-Si (a-Si:F).

In one embodiment, an optional thin a-Si cap layer (not shown) is deposited on the SiC layer **103**. The a-Si cap layer can act as a seed for gate oxidation. In another embodiment, this layer may be an oxide layer formed by an atomic layer deposition (ALD) process.

FIG. 2 illustrates additional fabrication steps of the present invention. This figure shows that the oxide-nitride-oxide (ONO) dielectric stack **200** for each transistor is formed over the SiC channel region layer **103**. The ONO dielectric stack **200** is formed for conventional SONOS memory cells. The nitride layer of the ONO dielectric **200** is the charge storage layer or floating gate.

Alternate embodiments may use other dielectric stacks depending on the desired cell characteristics. For example,  $\text{Al}_2\text{O}_3$ ,  $\text{HfO}_2$ ,  $\text{La}_2\text{O}_3$ ,  $\text{LaAlO}_3$ , and other suitable high dielectric constant (high-k) materials can be substituted for the nitride film. In another embodiment, the dielectric stack may have a graded stoichiometry, forming a “crested barrier” structure.

A control gate **205** is formed over the ONO stack **200**. The gate **205** can be polysilicon, metal, or some other suitable gate material. In one embodiment, the gate **205** is a p+ poly. Alternate embodiments may use n+ poly. A metal gate **205** can include metals such as TiN, TaN or some other suitable metal.

The spacers **201**, **202** are formed adjacent the transistor stack **200**, **205**. In one embodiment, the spacers **201**, **202** are an oxide. Alternate embodiments can use other materials.

Source and drain regions **210**, **211** are formed in the channel region layer **103**. In one embodiment, these are n+ doped regions in the SiC layer **103**. An alternate embodiment can use p+ regions. The source/drain regions **210**, **211** can be formed by conventional implants, solid-source diffusion, plasma doping schemes, or some other suitable method. In another embodiment, the source/drain regions **210**, **211** are formed utilizing gate-induced tunneling through Schottky barriers. In such devices, carrier injection is controlled by the modulation of the Schottky barrier width within a fully depleted source extension region.

In an alternate embodiment, the source/drain region implants are eliminated by forming source/drain contacts to the SiC thin film using metals and/or silicides with suitable work function to form low Schottky barrier contacts.

The function of each source/drain region **210**, **211** is determined by the biasing of the transistor. For example, a first region **210** may act like a drain region **210** when it is biased with a positive voltage and the remaining region **211** is a source region when it is at ground potential or left floating. An alternate embodiment can bias these regions **210**, **211** such that the functions reverse. During transistor operation, a channel forms in the channel region layer **103** between the source/drain regions **210**, **211**.

Metal deposition and pattern steps can be used to form Schottky contacts for the source/drain regions **210**, **211**. The contacts could be used to gain access to these regions **210**, **211**, for example, if they were formed on the top layer of a multiple transistor stack and required contact to interface with external connections and/or other circuits of the integrated circuit.

FIG. 3 illustrates another set of steps in fabricating the stacked non-volatile memory cells of the present invention. An oxide or other spacer material **300** is formed over the just completed transistor from FIG. 2. An oxide or other insulating layer **316** is then formed over this and the above described process is repeated for as many transistor stacks as desired.

The illustrated embodiment includes forming the second transistor **301** over the transistor of FIG. 2. The second transistor stack is comprised of the SiC or carbon rich silicon layer **315** over the oxide layer **316**. The source/drain regions **320**, **321** formed in the SiC channel region layer **315**. The transistor stack **303** comprising the ONO layer **310** and the control gate **311** is formed over the channel region layer **315** and the spacer material **312**, **313** is formed on either side of the transistor stack **303**.

In one embodiment, the carbon concentration is decreased in each subsequently formed transistor layer. In other words, the lowest transistor layer **330** will experience the greatest thermal budget. Therefore, the lowest layer **330** will have the greatest carbon content. The next layer of transistors **301** will experience somewhat less thermal processing and, thus, has less carbon concentration than the lower layer. The decrease in carbon content continues for each subsequently formed transistor layer. The carbon content can be tailored by changing the interstitial carbon concentration during SiC growth. Such an embodiment provides a first channel layer with superior short channel effects at the cost of a slight mobility reduction.

One embodiment of the above described stacked memory transistors uses 4H—SiC in the SiC layer **103**. 4H SiC has a band gap energy of 3.26 eV, thermal conductivity of 3.0-3.8 W/cm K at 300K and a breakdown electric field of  $2.2 \times 10^6$  V/cm. Another embodiment uses 6H—SiC that has a band gap energy of 3.03 eV, thermal conductivity of 3.0-3.8 W/cm K at 300K and a breakdown electric field of  $2.4 \times 10^6$  V/cm. These properties make it clear that SiC is an excellent material compared to silicon due to its very low leakage, high temperature operating characteristics, sustaining high electric fields, and excellent heat dissipation.

FIG. 4 illustrates a cross-sectional view of one embodiment of a three dimensional transistor in accordance with the thin film channel region layer of the present invention. The transistor is fabricated on a-Si **400** layer on the substrate. The channel region **420** between the source/drain regions **403**, **404** is a U-shaped region **420** that is formed in a thin layer of carbon rich silicon (SiC). In an alternate embodiment, SiC may be used for the channel region layer **401**.

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The ONO dielectric stack **410** fills the U-shaped area. A poly or metal gate **411** is formed over the ONO dielectric. As in previous embodiments, the nitride layer of the ONO stack **410** acts as the floating gate or charge storage layer.

The fabrication of the embodiment of FIG. **4** can be repeated multiple times to form a transistor stack of such non-planar transistors. This process has been discussed previously. The various alternate embodiments in fabrication and materials discussed previously can also be employed in these non-planar transistors.

FIG. **5** illustrates another non-planar embodiment of the present invention. This embodiment is a FinFET memory cell that employs the SiC/Si:C thin film channel region layer of the present invention.

The FinFET embodiment is comprised of a substrate **500** that, in one embodiment, is comprised of silicon. Two source/drain regions **501**, **502** are formed in a three dimensional manner over the substrate **500**. A silicon "fin" **503** is formed between the source/drain regions **501**, **502**. A gate **504** is formed over the silicon "fin" **503**. The gate can be a poly or metal gate. The gate is shown in dotted lines for purposes of clarity.

The "fin" **503** contains the Si:C/SiC channel region of the present invention. The structure of the "fin" **503** is shown in FIG. **6** and described subsequently. The percentage of carbon added to the amorphous silicon decreases for each subsequently formed layer of vertically stacked FinFET memory cells.

The FinFET of FIG. **5** is a double or triple gate transistor. The transistor is a double gate if the gate oxide (**601** of FIG. **6**) between the gate **504** and the "fin" is greater on the side-walls of the "fin" than the top. The transistor is a triple gate structure if the gate oxide is the same thickness on all three surfaces.

FIG. **6** shows a cross-sectional view, along axis A-A', of the FinFET embodiment of FIG. **5**. This view shows the substrate **500** over which the channel region **610**, the ONO layer **611**, and the Si:C or SiC thin film layer **503** is formed as shown in the three dimensional view of FIG. **5**.

This view additionally shows the gate oxide layer **601** that is formed over the "fin". While FIG. **6** shows this layer **601** to be of equal thickness over each surface, as would be the case in a triple gate structure, alternate embodiments can vary the thickness as previously described. For example, for a double gate device, the top surface of the "fin" would not be as thick as the sidewalls.

The gate **504** is formed over the gate oxide layer **601**. The gate **504** can be comprised of polysilicon, metal, or some other suitable gate material.

The fabrication of the embodiment of FIGS. **5** and **6** can be repeated multiple times to form a three dimensional transistor stack, as illustrated in the embodiment of FIG. **3**, of such non-planar transistors. This process has been discussed previously. The various alternate embodiments in fabrication and materials discussed previously can also be employed in these non-planar transistors.

FIG. **7** illustrates a functional block diagram of a memory device **700** that can incorporate the stacked non-volatile memory cells of the present invention. The memory device **700** is coupled to a processor **710**. The processor **710** may be a microprocessor or some other type of controlling circuitry. The memory device **700** and the processor **710** form part of an electronic memory system **720**. The memory device **700** has been simplified to focus on features of the memory that are helpful in understanding the present invention.

The memory device includes an array of non-volatile memory cells **730** that can be floating gate flash memory

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cells. The memory array **730** is arranged in banks of rows and columns. The control gates of each row of memory cells are coupled with a word line while the drain regions of the memory cells are coupled to bit lines. The source regions of the memory cells are coupled to source lines. As is well known in the art, the connection of the cells to the bit lines and source lines depends on whether the array is a NAND architecture, a NOR architecture, an AND architecture or some other memory array architecture. The stacked non-volatile memory cells of the present invention can operate in any memory array architecture.

An address buffer circuit **740** is provided to latch address signals provided on address input connections A0-Ax **742**. Address signals are received and decoded by a row decoder **744** and a column decoder **746** to access the memory array **730**. It will be appreciated by those skilled in the art, with the benefit of the present description, that the number of address input connections depends on the density and architecture of the memory array **730**. That is, the number of addresses increases with both increased memory cell counts and increased bank and block counts.

The memory integrated circuit **700** reads data in the memory array **730** by sensing voltage or current changes in the memory array columns using sense/buffer circuitry **750**. The sense/buffer circuitry, in one embodiment, is coupled to read and latch a row of data from the memory array **730**. Data input and output buffer circuitry **760** is included for bi-directional data communication over a plurality of data connections **762** with the controller **710**. Write circuitry **755** is provided to write data to the memory array.

Control circuitry **770** decodes signals provided on control connections **772** from the processor **710**. These signals are used to control the operations on the memory array **730**, including data read, data write, and erase operations. The control circuitry **770** may be a state machine, a sequencer, or some other type of controller.

The non-volatile memory device illustrated in FIG. **7** has been simplified to facilitate a basic understanding of the features of the memory. A more detailed understanding of internal circuitry and functions of flash memories are known to those skilled in the art.

FIG. **8** is an illustration of an exemplary memory module **800**. Memory module **800** is illustrated as a memory card, although the concepts discussed with reference to memory module **800** are applicable to other types of removable or portable memory, e.g., USB flash drives, and are intended to be within the scope of "memory module" as used herein. In addition, although one example form factor is depicted in FIG. **8**, these concepts are applicable to other form factors as well.

In some embodiments, memory module **800** will include a housing **805** (as depicted) to enclose one or more memory devices **810**, though such a housing is not essential to all devices or device applications. At least one memory device **810** is a non-volatile memory [including or adapted to perform elements of the invention]. Where present, the housing **805** includes one or more contacts **815** for communication with a host device. Examples of host devices include digital cameras, digital recording and playback devices, PDAs, personal computers, memory card readers, interface hubs and the like. For some embodiments, the contacts **815** are in the form of a standardized interface. For example, with a USB flash drive, the contacts **815** might be in the form of a USB Type-A male connector. For some embodiments, the contacts **815** are in the form of a semi-proprietary interface, such as might be found on COMPACTFLASH memory cards licensed by SANDISK Corporation, MEMORYSTICK memory cards

licensed by SONY Corporation, SD SECURE DIGITAL memory cards licensed by TOSHIBA Corporation and the like. In general, however, contacts **815** provide an interface for passing control, address and/or data signals between the memory module **800** and a host having compatible receptors for the contacts **815**.

The memory module **800** may optionally include additional circuitry **820** which may be one or more integrated circuits and/or discrete components. For some embodiments, the additional circuitry **820** may include a memory controller for controlling access across multiple memory devices **810** and/or for providing a translation layer between an external host and a memory device **810**. For example, there may not be a one-to-one correspondence between the number of contacts **815** and a number of I/O connections to the one or more memory devices **810**. Thus, a memory controller could selectively couple an I/O connection (not shown in FIG. **8**) of a memory device **810** to receive the appropriate signal at the appropriate I/O connection at the appropriate time or to provide the appropriate signal at the appropriate contact **815** at the appropriate time. Similarly, the communication protocol between a host and the memory module **800** may be different than what is required for access of a memory device **810**. A memory controller could then translate the command sequences received from a host into the appropriate command sequences to achieve the desired access to the memory device **810**. Such translation may further include changes in signal voltage levels in addition to command sequences.

The additional circuitry **820** may further include functionality unrelated to control of a memory device **810** such as logic functions as might be performed by an ASIC (application specific integrated circuit). Also, the additional circuitry **820** may include circuitry to restrict read or write access to the memory module **800**, such as password protection, biometrics or the like. The additional circuitry **820** may include circuitry to indicate a status of the memory module **800**. For example, the additional circuitry **820** may include functionality to determine whether power is being supplied to the memory module **800** and whether the memory module **800** is currently being accessed, and to display an indication of its status, such as a solid light while powered and a flashing light while being accessed. The additional circuitry **820** may further include passive devices, such as decoupling capacitors to help regulate power requirements within the memory module **800**.

## CONCLUSION

In summary, the non-volatile memory transistors of the present invention are fabricated on a silicon carbide or carbon rich silicon channel thin film. This provides reduced tunnel barrier and ease of erase with lower voltages and electric fields. The cells of the present invention are stackable in order to greatly increase the density of a memory device.

The non-volatile memory cells of the present invention may be NAND-type cells, NOR-type cells, or any other type of non-volatile memory array architecture.

Although specific embodiments have been illustrated and described herein, it will be appreciated by those of ordinary skill in the art that any arrangement that is calculated to achieve the same purpose may be substituted for the specific embodiments shown. Many adaptations of the invention will be apparent to those of ordinary skill in the art. Accordingly, this application is intended to cover any adaptations or variations of the invention. It is intended that this invention be limited only by the following claims and equivalents thereof.

What is claimed is:

**1.** A memory, comprising:

a first memory cell; and

a second memory cell formed over the first memory cell; wherein each of the first memory cell and the second memory cell comprises:

a channel region comprising silicon and carbon;

a control gate; and

a dielectric stack between the channel region and the control gate;

wherein a carbon concentration of the channel region of the second memory cell is less than a carbon concentration of the channel region of the first memory cell.

**2.** The memory of claim **1**, further comprising:

a third memory cell formed over the second memory cell; wherein the third memory cell comprises:

a channel region comprising silicon and carbon;

a control gate; and

a dielectric stack between the channel region and the control gate;

wherein a carbon concentration of the channel region of the third memory cell is less than the carbon concentration of the channel region of the second memory cell.

**3.** The memory of claim **1**, wherein each of the channel regions comprises silicon carbide.

**4.** The memory of claim **3**, wherein the silicon carbide is formed on amorphous silicon.

**5.** The memory of claim **4**, wherein the amorphous silicon is selected from the group consisting of hydrogenated amorphous silicon, deuterated amorphous silicon and fluorinated amorphous silicon.

**6.** The memory of claim **1**, wherein each of the channel regions comprises carbon-rich amorphous silicon.

**7.** The memory of claim **1**, wherein each of the dielectric stacks comprises a charge storage dielectric.

**8.** The memory of claim **7**, wherein the charge storage dielectric comprises silicon nitride.

**9.** The memory of claim **7**, wherein the charge storage dielectric comprises a high-k dielectric.

**10.** The memory of claim **9**, wherein the high-k dielectric is selected from the group consisting of  $\text{Al}_2\text{O}_3$ ,  $\text{HfO}_2$ ,  $\text{LaO}_3$  and  $\text{LaAlO}_3$ .

**11.** The memory of claim **1**, wherein each of the first memory cell and the second memory cell further comprises source/drain regions.

**12.** The memory of claim **11**, wherein the source/drain regions for each of the first memory cell and the second memory cell are formed on opposing ends of their respective channel region.

**13.** The memory of claim **11**, wherein the source/drain regions for each of the first memory cell and the second memory cell are formed in their respective channel region adjacent opposing sides of their respective control gate.

**14.** A memory, comprising:

a plurality of memory cells formed in a stack;

wherein each memory cell of the stack of memory cells comprises:

a channel region comprising carbon-rich amorphous silicon;

a control gate; and

a dielectric stack between the channel region and the control gate,

wherein the dielectric stack comprises a charge storage dielectric;

wherein the channel region of each memory cell of the stack of memory cells has an associated predetermined concentration of carbon;

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wherein the stack of memory cells comprises a particular memory cell and an other memory cell;  
 wherein the other memory cell is formed over the particular memory cell in the stack of memory cells; and  
 wherein the predetermined carbon concentration of the channel region of the other memory cell is less than the predetermined carbon concentration of the channel region of the particular memory cell.

**15.** The memory of claim **14**, wherein the predetermined carbon concentration of the channel region of any memory cell of the stack of memory cells is less than the predetermined carbon concentration of the channel region of each other memory cell of the stack of memory cells formed underneath it in the stack of memory cells.

**16.** The memory of claim **14**, wherein each memory cell of the stack of memory cells further comprises source/drain regions formed on opposing ends of their respective channel region.

**17.** A memory, comprising:  
 a plurality of memory cells formed in a stack;  
 wherein each memory cell of the stack of memory cells comprises:  
     a channel region comprising carbon-rich amorphous silicon;  
     a control gate; and  
     a dielectric stack between the channel region and the control gate,

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wherein the dielectric stack comprises a charge storage dielectric;

wherein the channel region of each memory cell of the stack of memory cells has an associated interstitial carbon concentration;

wherein the stack of memory cells comprises a particular memory cell and an other memory cell;

wherein the other memory cell is formed over the particular memory cell in the stack of memory cells; and

wherein the interstitial carbon concentration of the channel region of the other memory cell is less than the interstitial carbon concentration of the channel region of the particular memory cell.

**18.** The memory of claim **17**, wherein the interstitial carbon concentration of the channel region of any memory cell of the stack of memory cells is less than the interstitial carbon concentration of the channel region of each other memory cell of the stack of memory cells formed underneath it in the stack of memory cells.

**19.** The memory of claim **17**, wherein the silicon carbide comprises a silicon carbide selected from the group consisting of 4H—SiC and 6H—SiC.

**20.** The memory of claim **17**, wherein each memory cell of the stack of memory cells further comprises source/drain regions formed in their respective channel region adjacent opposing sides of their respective control gate.

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